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MoSi₂价电子结构分析及结合能计算

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摘要: 根据固体与分子经验电子理论, 通过键距差(BLD)方法, 计算了金属间化合物MoSi₂的价电子结构和理论结合能。结果表明, MoSi₂理论结合能为1 677.1 kJ/mol, 与实验值吻合。由于Si原子偏移, 沿〈001〉方向分布的Si—Si原子键共价电子数最多, $n_D=0.402\ 04$ 。MoSi₂晶体中含有较高密度的晶格电子, 使MoSi₂具有良好的导电性。MoSi₂晶体中键络分布不均匀性是导致晶体脆性的主要原因。

关键字: 二硅化钼; 价电子; 结合能; 脆性

Valence electronic structure analysis and cohesive energy calculation of MoSi₂

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Abstract: According to the empirical electron theory of solid and molecule, the valence electron structure and theoretical cohesive energy of MoSi₂ were calculated by the BLD method. The results show that the theoretical cohesive energy of MoSi₂ is 1 677.1 kJ/mol, which agrees well with the experimental data. Because of a shift in Si positions, the valence electrons between Si—Si atoms along <001> direction are the most ($n_D = 0.402\ 04$). There are lattice electrons with higher densities in MoSi₂, which accounts for the good conductivity of MoSi₂. Also, it is speculated that the brittleness of MoSi₂ can be explained primarily by a heterogeneity of bond distribution.

Key words: molybdenum disilicide; valence electron; cohesive energy; brittleness

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